SiPM Workshop

from fundamental research
to industrial applications
Bari, Italy, 2-4 October 2019

Packaging strategies for large SiPM-based cryogenic photo-detectors

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VINCENZO DE VIRGILIO

LIGHT DETECTION IN DARK SIDE



DarkSide is a stepped program for the realization of increasing size dark matter direct detection on a liquid argon target. The current detector, DarkSide-50, is located at LNGS and using 50 kg of UAr inside a dual-phase Time Projection Chamber (TPC)

- Interaction in the active volume produces **scintillation light (SI)** and ionization electrons. SI is detected by photosensors (like PMTs) on top and bottom of the TPC.
- Electrons are drifted by means of an electric field to the liquid-gas interface and extracted in the gas phase and accelerated toward the anode. The interaction between e- and the gas produces electroluminescence light (S2), detected by the photosensors.
- The presence of S1 and S2 allows to reconstruct the position of the original interaction allowing fiducialization
- The shape of S1 allows the discrimination of nuclear recoils from electromagnetic interaction (PSD) with a rejection better than 10⁸
- Other discriminations are possible to further reduce the Background (S2/S1, multi-site interactions, ...)



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PDM photodetector module

- SiPMs are small size devices (tens to hundreds of mm²)
- A solution is to group SiPMs in arrays of size comparable to that of PMTs and read out this array (tile) as a single channel with appropriate electronics
- Tile + electronics form a PhotoDetector Module (PDM)
- About 10000 PDMs are foreseen
 - The production procedures (electronics & packaging) will require high reliability

Requirements:

- ▶ 25 cm² surface (8280 channels in total)
- ▶ overall PDE > 40% at 420 nm
- ▶ dynamic range > 50 pe
- ▶ time resolution of O(10 ns)
- ▶ overall noise rate below 0.1 Hz/mm²







PDM PERFORMANCES





- The PDM integrates the SiPM tile and the readout electronics inside an acrylic cage
- 24 cm² total active surface
 - $24 \times 8 \times 12 \text{ mm}^2 \text{ SiPMs}$
- SiPMs are from FBK developed for low after and low dark rate operation in liquid argon.





MOTHERBOARD



- Mechanical structure required to assemble all components and to efficiently dissipate heat in LAr target, minimizing the production of bubbles
- power dissipation density limited to 100 µW/mm², corresponding to a total dissipated power of 250 mW per PDM
- signal extraction via analog optical transmission
- each PDM can be turned on and off individually
- goal radio purity ~ 10 mBq/MB
 3" PMT can be ~ few mBq

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Problems:

- I. CTE of substrate
- 2. Radio-Purity
- 3. Bonding reliability
- 4. Anode contact

Requirements:

- Low CTE substrate
 - with good rigidity
- High Radio-Purity
 - ~ few mBq/m² for U/Th chains and for 40 K
- >> 99% die bonding reliability in LAr
 - 0.99²⁴ = 79% yield for PDM
- TSV to avoid wire bonding



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PACKAGING SOLUTIONS FOR CRYOGENIC APPLICATIONS

CTE of substrate

Radio-Purity

Bonding strategies Anode contact

Material	CTE [ppm/K]	U/Th [mBq/kg]	⁴⁰ K [mBq/kg]
Silicon	3-5	very low	very low
FR4	12-14	very high	very high
PTFE/Teflon	120	0. - 0	<5
Polyimide/ Kapton	20	1-10	< 0
Arlon NT	5-7	100	1000
Fused Silica	0.5	5-20	-
Selected FS	0.5	0.05	-



- Stress on SiPM due to difference of CTE
- R&D on substrate
 - Silicon PCBs are not trivial: Si is not an insulator
 - Multilayer Fused Silica PCBs require die bonding
 - Pyralux-Invar-Pyralux
- Arlon NT is readily available

CTE of substrate

Radio-Purity

Bonding strategies Anode contact

Material	CTE [ppm/K]	U/Th [mBq/kg]	⁴⁰ K [mBq/kg]
Silicon	3-5	very low	very low
FR4	2- 4	very high	very high
PTFE/Teflon	120	0.1-10	<5
Polyimide/ Kapton	20	1-10	<10
Arlon NT	5-7	100	1000
Fused Silica	0.5	5-20	-
Selected FS	0.5	0.05	_

- Arlon is at the edge of DS-20k acceptance for radio-purity: R&D on other solutions is ongoing
- components $\sim 60 \, \mu Bq/kg$
- main background from substrate (at this moment)

CTE of substrate

Radio-Purity

Bonding strategies epoxy bonding Anode contact

Current procedure uses robot dispenser plus a manual die bonder.

<image>

Temporary solution:

- cryo-graded conductive epoxy bonding
 - EPO-TEK EJ2189 cured at 100°C for 1h
 - the current TTiN SiPM backside does not allow other solutions.



CTE of substrate

Radio-Purity

Bonding strategiesreliability

tests done with fused silica dies





bonding force
dot size
number of dots

Anode contact

- too much epoxy can shortcut neighbor pads
- too less epoxy will not hold the SiPM

~1800 SiPMs successfully bonded

We performed many reliability tests in LN_2

Current reliability > 99.9%

CTE of substrate

Radio-Purity



Silver loaded epoxy is not radio-pure • and not reliable in the long term

We are moving to a new procedure:
indium/solder bump bonding
gold studs ball bonding
Both solutions were tested are provided very strong bonds

A procedure has already been defined. Final tests with first LFoundry wafers in November.

Bonding strategies▶ thermo-compression



Anode contact





CTE of substrate

Radio-Purity

Bonding strategies thermo-compression



Anode contact

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288 un round			on no	
258 un square			99 on Arl	
358 um round			In99.9	Kara

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350 Lin		Arlon	
258 un square		Pb37 on	
350 un round		Sn63/	



CTE of substrate

Radio-Purity

Bonding strategies

Anode contact

wire bonding

- 25 µm aluminium wire
- 24 wires per PDM

Very fragile during manipulation:

Complicated installation of the experiment



PACKAGING SOLUTIONS FOR CRYOGENIC APPLICATIONS CTE of substrate Radio-Purity Anode contact Bonding strategies TSV **Bottom view** FOUNDRY Solutions for great visions passivation openings with UBM (Cu+Ni+Au) (300×300µm) robustness and higher fill factor (97%) die backside and PCB topside modification thermo-compression bonding Side view TSV Silicon oxide passivation layer JBM cathode contacts passivation 7.9 mm with indium balls

* not to scale

MASS PRODUCTION



NOA is a project funded through the RESTART program which aims to re-launch the economy and advanced training in the 2009 earthquake region.

NOA is using top quality equipment for the packaging of silicon devices

NOA proposal starts in the framework of DarkSide-20k.

SiPMs will be produced by LFoundry and delivered to NOA CR.

NOA will include the following processes all available for wafers up to 8":

- cryogenic and room temperature wafer probing
- dicing
- fully automated flip-chip bonding

Moreover, NOA will include radio-pure processes for SMD PCB productions and an advanced electronic testing facility.



SCHEDULE

NOA will be commissioned next summer

- The cleanroom will be installed September 2020.
- The machines will be installed soon after.
- People have been hired and getting trained.

After that, DarkSide will start the production. The tuning of the process will take few months. The first MBs will be ready by the end of 2020. The production of 360 MBs will last ~1.5 years.

CONCLUSIONS

DarkSide-20k succeeded in an ambitious R&D program to deploy radio-pure cryo-graded, SiPM-based, large photodetector.

The hot topics include:

- development of a specific technology of SiPM within FBK for LAr
- development of an extremely low noise preamplifier board
- selection of radio-pure components
- identification and use of the most advanced silicon packaging techniques
- deployment of a cutting edge silicon packaging facility at LNGS